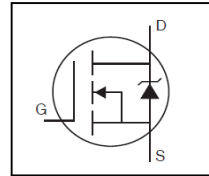


- Advanced Process Technology
- Isolated Package
- High Voltage Isolation = 2.5KVRMS ⑤
- Sink to Lead Creepage Dist. = 4.8mm
- Fully Avalanche Rated
- Lead-Free

HEXFET® Power MOSFET



$V_{DSS}$	<b>55V</b>
$R_{DS(on)}$	<b>0.016Ω</b>
$I_D$	<b>40A</b>



<b>G</b>	<b>D</b>	<b>S</b>
Gate	Drain	Source

**Description**

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-220 Full Pak eliminates the need for additional insulating hardware in commercial-industrial applications. The molding compound used provides a high isolation capability and a low thermal resistance between the tab and external heat sink. This isolation is equivalent to using a 100 micron mica barrier with standard TO-220 product. The Fullpak is mounted to a heat sink using a single clip or by a single screw fixing.

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFIZ48NPbF	TO-220 Full-Pak	Tube	50	IRFIZ48NPbF

**Absolute Maximum Ratings**

Symbol	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	40	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	29	
$I_{DM}$	Pulsed Drain Current ①⑥	210	
$P_D @ T_C = 25^\circ\text{C}$	Maximum Power Dissipation	54	W
	Linear Derating Factor	0.36	W/°C
$V_{GS}$	Gate-to-Source Voltage	± 20	V
$E_{AS}$	Single Pulse Avalanche Energy (Thermally Limited) ②⑥	270	mJ
$I_{AR}$	Avalanche Current ①⑥	32	A
$E_{AR}$	Repetitive Avalanche Energy ①	5.4	mJ
dv/dt	Peak Diode Recovery dv/dt③⑥	5.0	V/ns
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

**Thermal Resistance**

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	2.8	°C/W
$R_{\theta JA}$	Junction-to-Ambient	—	65	

**Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)**

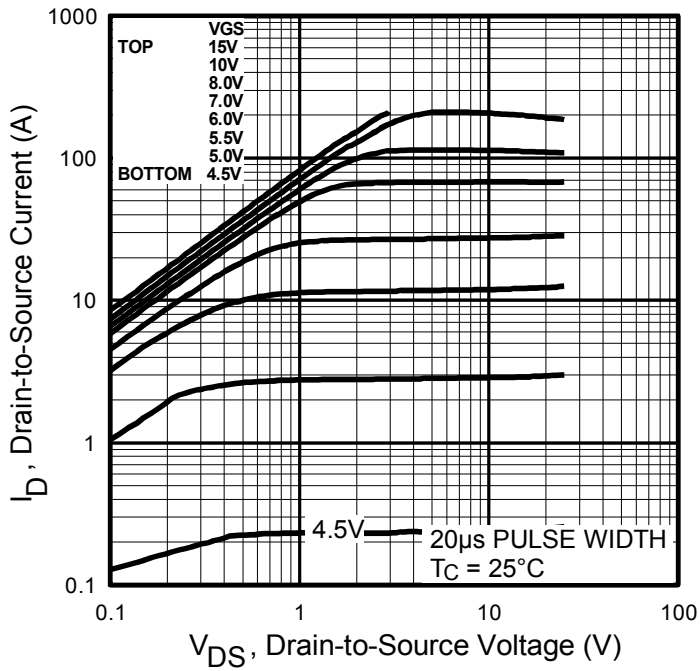
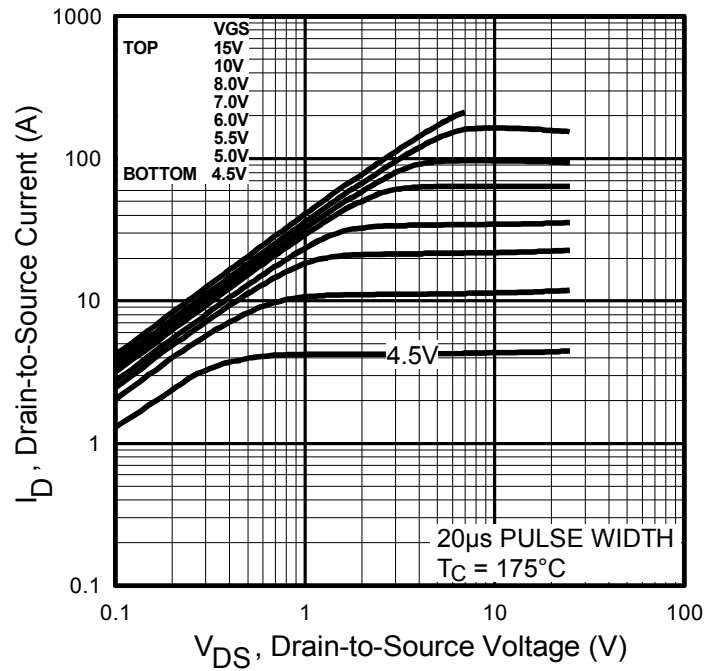
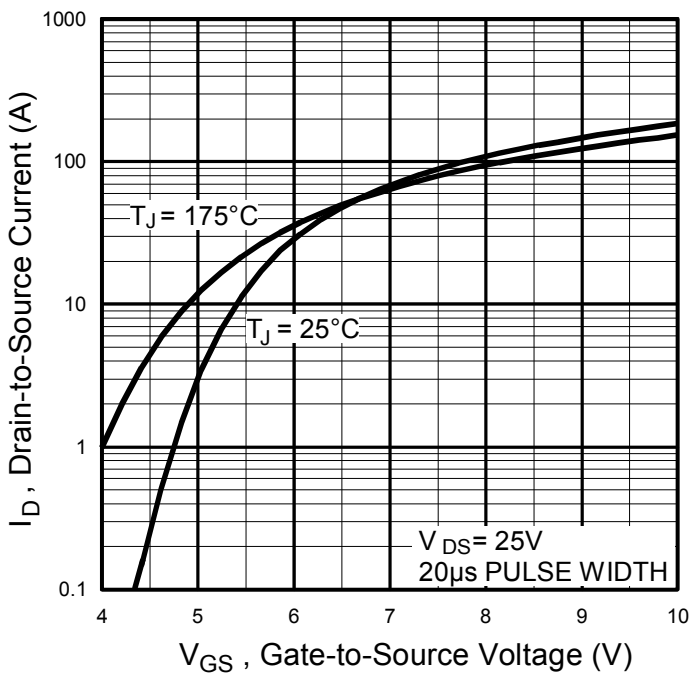
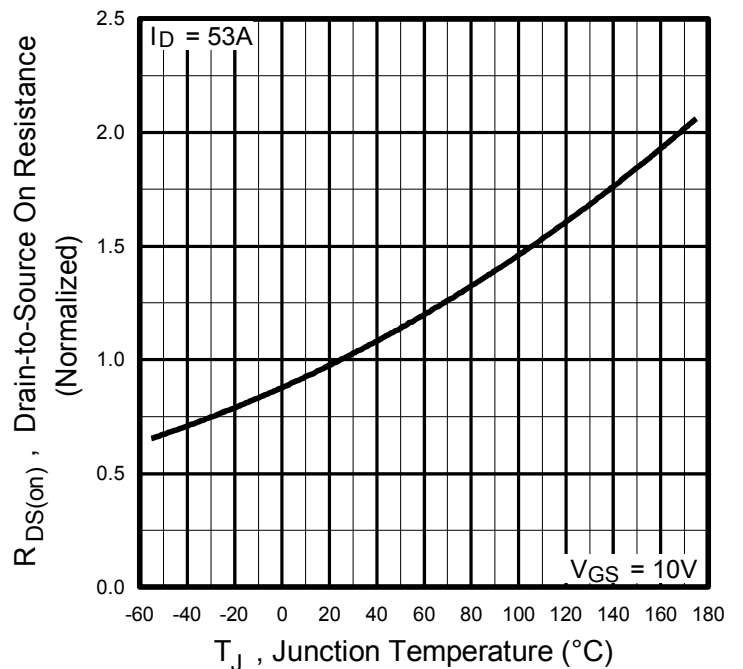
	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	55	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.052	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA ⑥
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	0.016	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 22A
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	—	4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
g <sub>fs</sub>	Forward Trans conductance	22	—	—	S	V <sub>DS</sub> = 25V, I <sub>D</sub> = 32A⑥
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	25	μA	V <sub>DS</sub> = 55V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 44V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 150°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -20V
Q <sub>g</sub>	Total Gate Charge	—	—	89	nC	I <sub>D</sub> = 32A
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	20		V <sub>DS</sub> = 44V
Q <sub>gd</sub>	Gate-to-Drain Charge	—	—	39		V <sub>GS</sub> = 10V, See Fig. 6 and 13④⑥
t <sub>d(on)</sub>	Turn-On Delay Time	—	11	—	ns	V <sub>DD</sub> = 28V
t <sub>r</sub>	Rise Time	—	78	—		I <sub>D</sub> = 32A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	32	—		R <sub>G</sub> = 5.1Ω
t <sub>f</sub>	Fall Time	—	48	—		R <sub>D</sub> = 0.85Ω, See Fig. 10④⑥
L <sub>D</sub>	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact:
L <sub>S</sub>	Internal Source Inductance	—	7.5	—		
C <sub>iss</sub>	Input Capacitance	—	1900	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	620	—		V <sub>DS</sub> = 25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	270	—		f = 1.0MHz, See Fig. 5⑥
C	Drain to Sink Capacitance	—	12	—		f = 1.0MHz

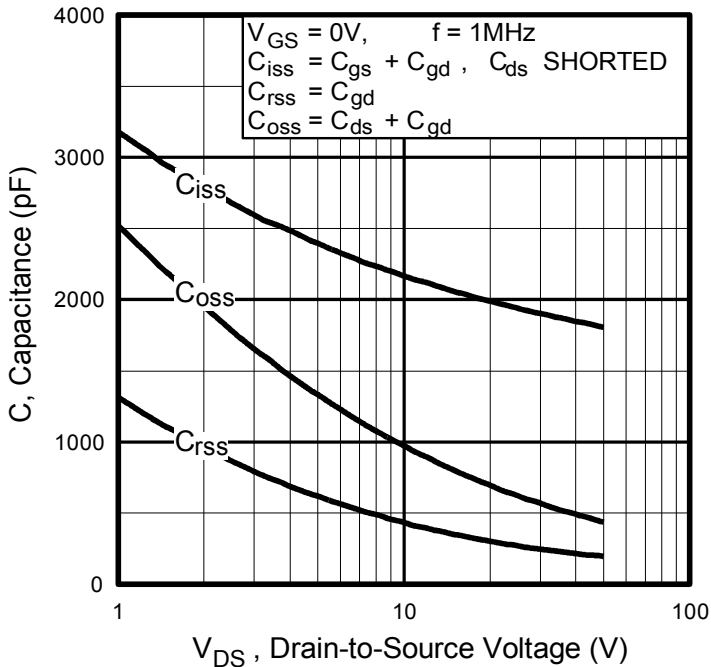
**Source-Drain Ratings and Characteristics**

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	49	A	MOSFET symbol showing the integral reverse p-n junction diode.
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	210		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 22A, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	94	140	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 32A
Q <sub>rr</sub>	Reverse Recovery Charge	—	360	540	nC	di/dt = 100A/μs ④⑥

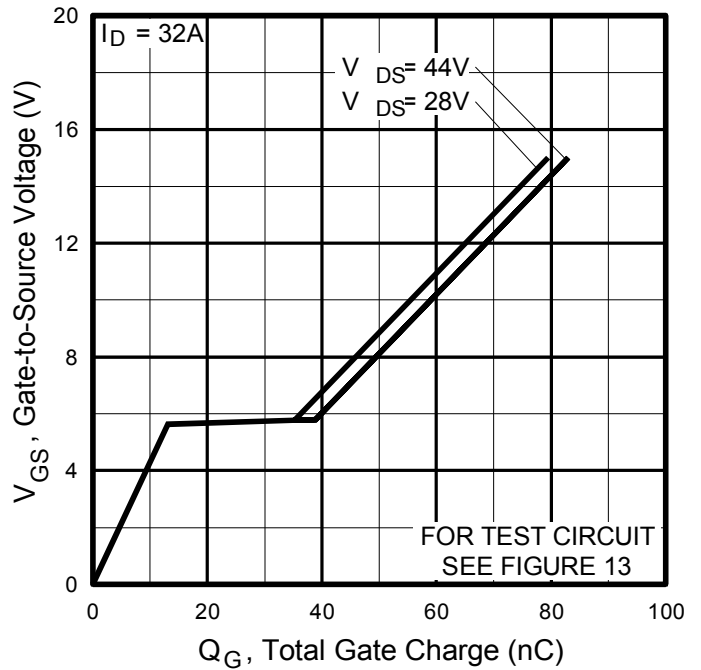
**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② V<sub>DD</sub> = 25V, starting T<sub>J</sub> = 25°C, L = 530μH, R<sub>G</sub> = 25Ω, I<sub>AS</sub> = 32A (See fig. 12)
- ③ I<sub>SD</sub> ≤ 32A, di/dt ≤ 250A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>J</sub> ≤ 175°C.
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ t = 60s, f = 60Hz
- ⑥ Uses IRFZ48N data and test conditions.

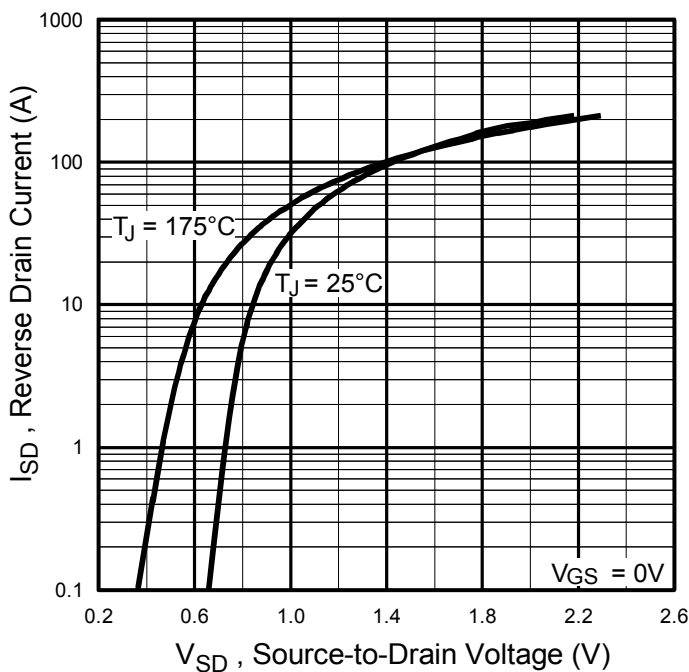

**Fig. 1** Typical Output Characteristics

**Fig. 2** Typical Output Characteristics

**Fig. 3** Typical Transfer Characteristics

**Fig. 4** Normalized On-Resistance vs. Temperature



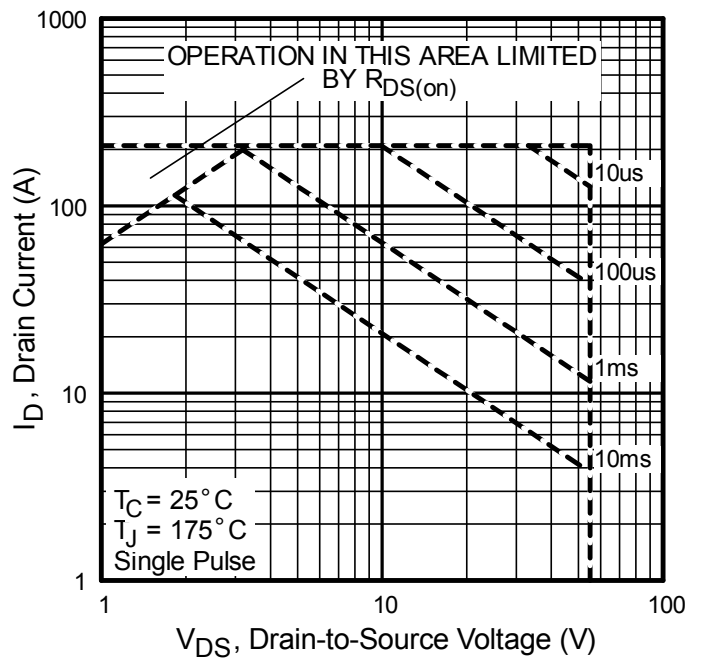
**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage



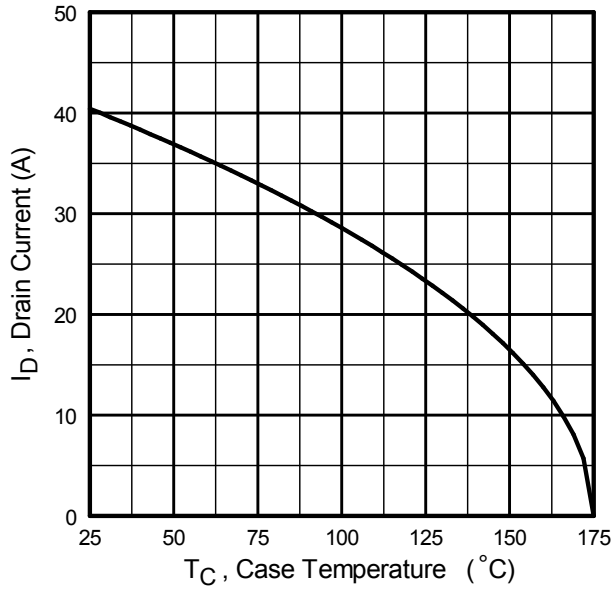
**Fig 6.** Typical Gate Charge vs. Gate-to-Source Voltage



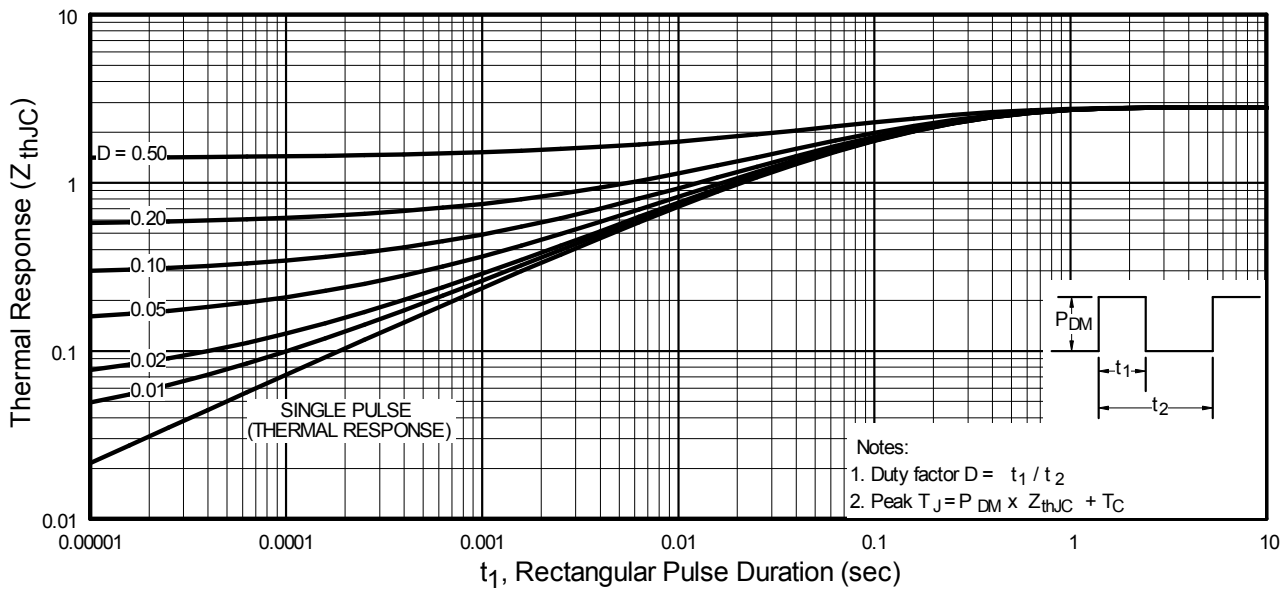
**Fig. 7** Typical Source-to-Drain Diode Forward Voltage

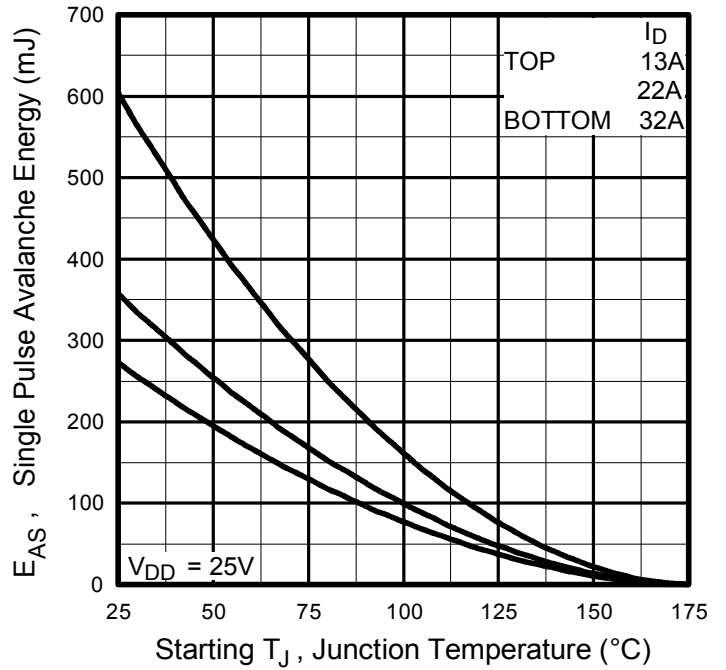


**Fig 8.** Maximum Safe Operating Area

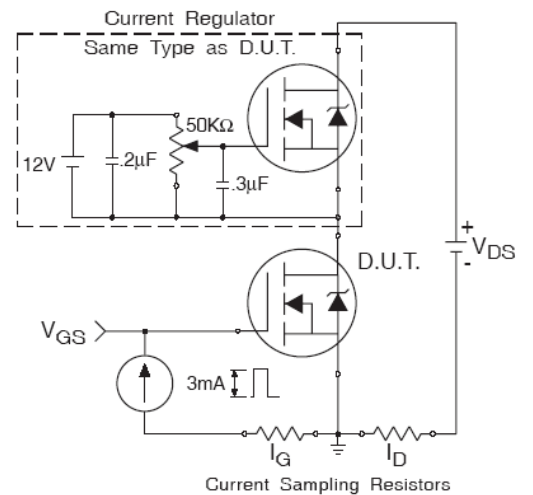

**Fig 9.** Maximum Drain Current vs. Case Temperature

**Fig 10a.** Switching Time Test Circuit

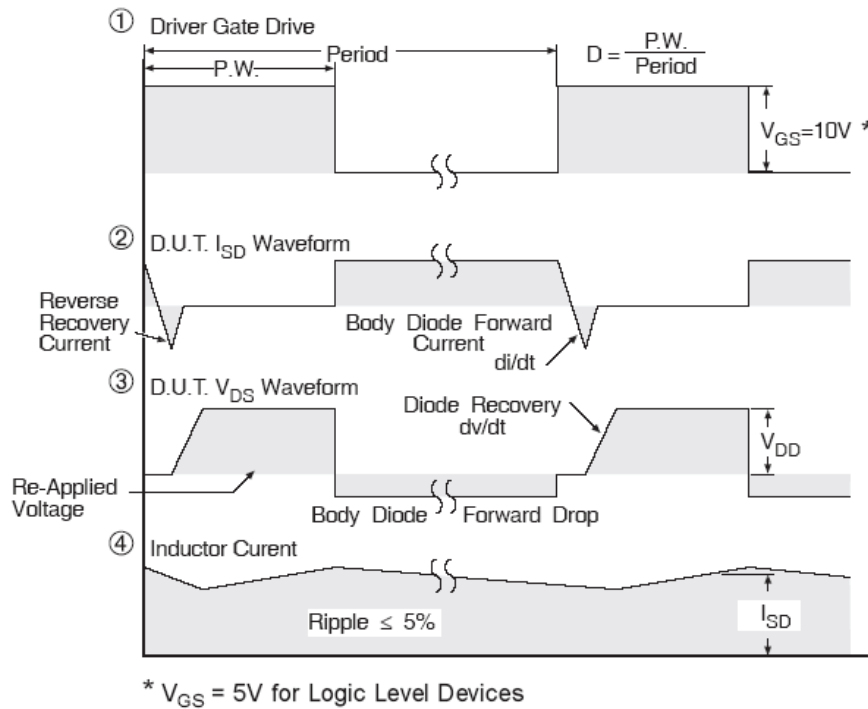
**Fig 10b.** Switching Time Waveforms

**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case


**Fig 12a. Unclamped Inductive Test Circuit**

**Fig 12c. Maximum Avalanche Energy vs. Drain Current**

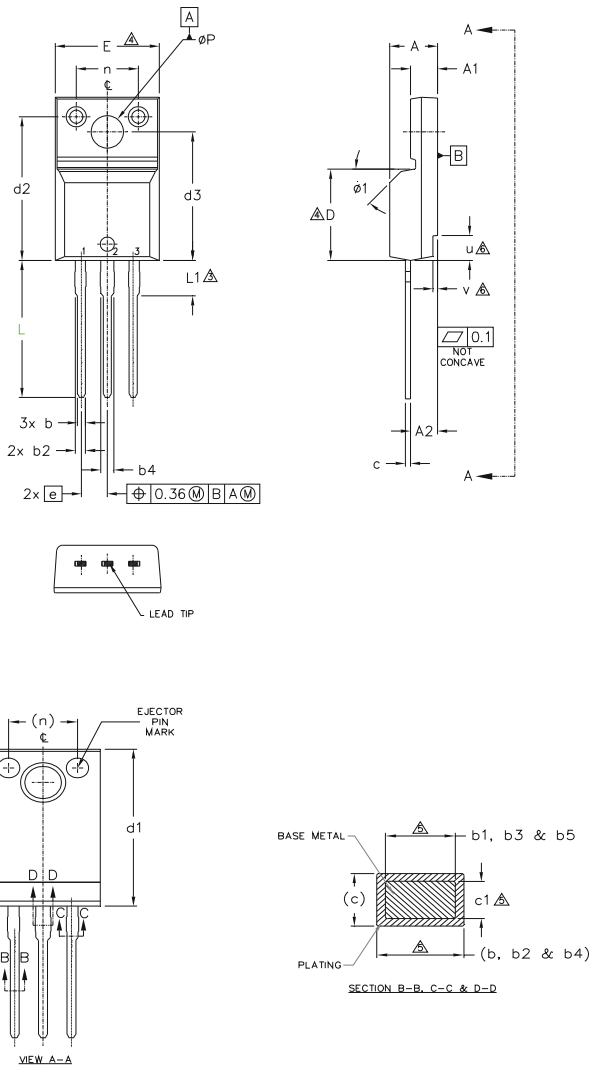
**Fig 12b. Unclamped Inductive Waveforms**

**Fig 13a. Gate Charge Waveform**

**Fig 13b. Gate Charge Test Circuit**

### Peak Diode Recovery dv/dt Test Circuit



**Fig 14.** Peak Diode Recovery  $dv/dt$  Test Circuit for N-Channel HEXFET® Power MOSFETs

**TO-220 Full-Pak Package Outline (Dimensions are shown in millimeters (inches))**

**NOTES:**

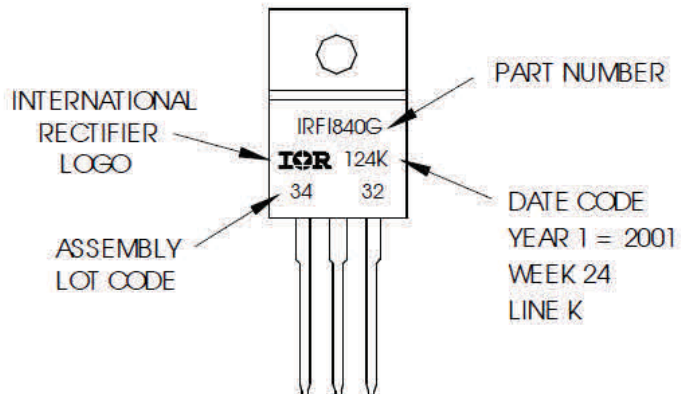
- 1.0 DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
- 2.0 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3.0 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
- 4.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTER MOST EXTREMES OF THE PLASTIC BODY.
- 5.0 DIMENSION b1, b3, b5 & c1 APPLY TO BASE METAL ONLY.
- 6.0 STEP OPTIONAL ON PLASTIC BODY DEFINED BY DIMENSIONS u & v.
- 7.0 CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.57	4.83	.180	.190	LEAD ASSIGNMENTS  HEXFET 1.- GATE 2.- DRAIN 3.- SOURCE  IGBTs, CoPACK 1.- GATE 2.- COLLECTOR 3.- EMITTER
A1	2.57	2.82	.101	.111	
A2	2.51	2.92	.099	.115	
b	0.61	0.94	.024	.037	
b1	0.61	0.89	.024	.035	
b2	0.76	1.27	.030	.050	
b3	0.76	1.22	.030	.048	
b4	1.02	1.52	.040	.060	
b5	1.02	1.47	.040	.058	
c	0.33	0.63	.013	.025	
c1	0.33	0.58	.013	.023	
D	8.66	9.80	.341	.386	
d1	15.80	16.13	.622	.635	
d2	13.97	14.22	.550	.560	
d3	12.29	12.93	.484	.509	
E	9.63	10.74	.379	.423	
e	2.54 BSC		.100 BSC		
L	13.21	13.72	.520	.540	
L1	3.10	3.68	.122	.145	
n	6.05	6.60	.238	.260	
phi P	3.05	3.45	.120	.136	
u	2.39	2.49	.094	.098	
v	0.41	0.51	.016	.020	
phi 1	-	45°	-	45°	

**TO-220 Full-Pak Part Marking Information**

EXAMPLE: THIS IS AN IRF1840G  
 WITH ASSEMBLY  
 LOT CODE 3432  
 ASSEMBLED ON WW 24, 2001  
 IN THE ASSEMBLY LINE "K"

Note: "P" in assembly line position  
 indicates "Lead-Free"



TO-220AB Full-Pak packages are not recommended for Surface Mount Application.

Note: For the most current drawing please refer to website at <http://www.irf.com/package/>



**Qualification Information**

<b>Qualification Level</b>	Industrial (per JEDEC JESD47F) †	
<b>Moisture Sensitivity Level</b>	TO-220 Full-Pak	N/A
<b>RoHS Compliant</b>	Yes	

† Applicable version of JEDEC standard at the time of product release.

**Revision History**

Date	Comments
04/27/2017	<ul style="list-style-type: none"> <li>Changed datasheet with Infineon logo - all pages.</li> <li>Corrected Package Outline on page 8.</li> <li>Added disclaimer on last page.</li> </ul>

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